New Jersey Semi-Conductor Products, Inc.

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MRF501 (SILICON)
MRF502

The RF Line

NPN SILICON RF SMALL-SIGNAL TRANSISTORS

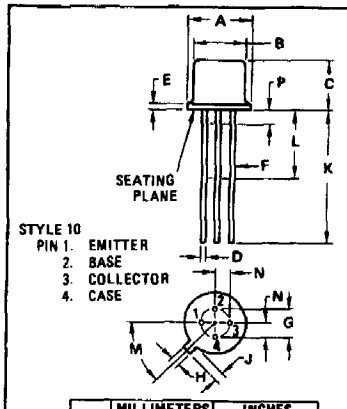
. . . designed primarily for use in high-gain, low-noise amplifier, oscillator, and mixer applications. Can also be used in UHF converter applications.

- High Current-Gain – Bandwidth Product –
  f_T = 1.2 GHz (Typ) @ I_C = 5.0 mAdc
- Low Noise Figure –
  NF = 4.0 dB (Typ) @ f = 200 MHz

NPN SILICON RF SMALL-SIGNAL TRANSISTORS

MAXIMUM RATINGS

Rating	Symbol	MRF501	MRF502	Unit
Collector-Emitter Voltage	V_{CEO}	15		Vdc
Collector-Base Voltage	V_{CBO}	25	35	Vdc
Emitter-Base Voltage	V_{EBO}	3.5		Vdc
Collector Current	I_C	50		mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	200 1.14		mW mW/°C
Storage Temperature Range	T_{stg}	-65 to +200		°C



STYLE 10
PIN 1. EMITTER
2. BASE
3. COLLECTOR
4. CASE

DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	5.31	5.84	0.209	0.230
B	4.52	4.95	0.178	0.195
C	4.32	5.33	0.170	0.210
D	0.41	0.53	0.016	0.021
E	–	0.76	–	0.030
F	0.41	0.48	0.016	0.019
G	2.54 BSC		0.100 BSC	
H	0.91	1.17	0.036	0.046
J	0.71	1.22	0.028	0.048
K	12.70	–	0.500	–
L	6.35	–	0.250	–
M	45° BSC		45° BSC	
N	1.27 BSC		0.050 BSC	
P	–	1.27	–	0.050

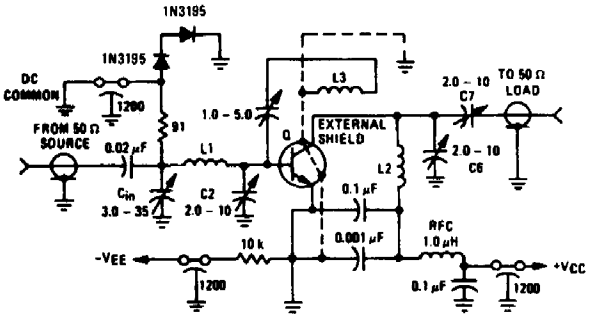
ALL JEDEC dimensions and notes apply

Quality Semi-Conductors

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Collector-Emitter Breakdown Voltage (I_C = 3.0 mAdc, I_B = 0)		BV_{CEO}	15	–	–	Vdc
Collector-Base Breakdown Voltage (I_C = 1.0 μAdc, I_E = 0)	MRF501 MRF502	BV_{CBO}	25 35	– –	– –	Vdc
Emitter-Base Breakdown Voltage (I_E = 1.0 μAdc, I_C = 0)		BV_{EBO}	3.5	–	–	Vdc
Collector Cutoff Current (V_{CB} = 1.0 Vdc, I_E = 0)	MRF501 MRF502	I_{CBO}	– –	– –	50 20	nAdc
ON CHARACTERISTICS						
DC Current Gain (I_C = 1.0 mAdc, V_{CE} = 6.0 Vdc)	MRF501 MRF502	h_{FE}	30 40	– –	250 170	–
DYNAMIC CHARACTERISTICS						
Current Gain – Bandwidth Product (I_C = 5.0 mAdc, V_{CE} = 6.0 Vdc, f = 100 MHz)	MRF501 MRF502	f_T	600 800	1000 1200	– –	MHz
Collector-Base Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 0.1 to 1.0 MHz)		C_{cb}	–	0.6	–	pF
Collector-Base Time Constant (I_E = 2.0 mAdc, V_{CB} = 6.0 Vdc, f = 31.8 MHz)		$r_b'C_c$	–	8.0	–	ps
Noise Figure (Figure 1) (I_C = 1.5 mAdc, V_{CE} = 6.0 Vdc, R_S = 50 ohms, f = 200 MHz)	MRF501 MRF502	NF	– –	4.5 4.0	– –	dB
FUNCTIONAL TEST						
Common-Emitter Amplifier Power Gain (Figure 1) (V_{CC} = 6.0 Vdc, I_C = 5.0 mAdc, f = 200 MHz)	MRF501 MRF502	G_{pe}	– –	15 17	– –	dB

FIGURE 1 – 200 MHz AMPLIFIER POWER GAIN AND NOISE FIGURE CIRCUIT



L1 1 3/4 Turns, #18 AWG, 0.5" Long, 0.5" Diameter
L2 2 Turns, #16 AWG, 0.5" Long, 0.5" Diameter
L3 2 Turns, #18 AWG, 0.25" Long, 0.5" Diameter, Position Approximately 0.25" from L2